

ON Semiconductor

Is Now



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ON Semiconductor

DN05104/D

Design Note – DN05104/D

45W TYPE-C PD3.0 / QC3.0 Power Adapter Solution with WT6632F

ON's Device	Application	Input Voltage	Output Power	Topology	I/O Isolation
NCP1342AMDAAD1					
NCP4306AADZZZA	Smart phone, PAD and NB adapter supporting PD3.0 and QC3.0	90 Vac to 264 Vac	45 W	Flyback	Isolated (3 kV)
NTMFS6B03					
ATP104					

	PD Output Specification	QC Output Specification
Output Voltage	5 V, 9 V, 12 V, 15 V, 20 V	5 V, 9 V, 12 V
Nominal Current	5V/3A, 9V/3A, 12V/3A, 15V3A, 20V/2.25A	5 V / 3 A, 9 V / 3 A, 12 V / 3 A
Max Current	5V/3A, 9V/3A, 12V/3A, 15V3A, 20V/2.25A	5 V / 3 A, 9 V / 3 A, 12 V / 3 A
Min Current	zero	zero

Avg. Efficiency	>91% @ 20 V 2.25 A at board end, 115 & 230 Vac
Ripple	<100mV
Standby Power	<30mW @ 5 V & 230 Vac (No cable plug in)
Power Density	1.15W/cm^3
Protection	Adaptive UVP, OVP, SCP, OTP
Size	57mmx36mmx19mm

Circuit Description

This design note describes a 45 W, Type C interface PD3.0, universal AC input, constant voltage power supply intended for smart phone, PAD and NB adaptor supporting PD3.0 or QC3.0 protocol, where isolation from the AC mains is required, and low cost, high efficiency, and low standby power are essential.

The featured power supply is a simple QR flyback topology utilizing ON Semiconductor's NCP1342 HF PWM controller, NCP4306D synchronous rectified controller, NTMFS6B03 synchronous MOSFET and ATP104 Switch MOSFET. This Design Note provides the complete circuit schematic details, PCB and BOM for 45 W Type C Interface PD3.0 Power adapter solution which supports PD output (5 V / 3 A, 9 V / 3 A, 12 V / 3 A, 15 V / 3 A, 20 V / 2.25 A).

This design combined with Weltrend WT6632F PD3.0 protocol controller to provide PD3.0 and

QC3.0 functions. This design also proposes a dual auxiliary power supply to supply PWM controller, the PWM controller is supplied by high voltage auxiliary voltage at low output voltage and supplied by low voltage auxiliary voltage at high output voltage and also shuts down zener bias of high voltage Vcc while low voltage auxiliary voltage supplies controller.

This design also uses NCP4306 synchronous rectified controller to provide high efficiency and also has no external Vcc regulator to supply synchronous controller to ensure controller can work below 3.6 V.

Key Features

- Universal AC input range (90 – 264 Vac)
- Very low standby (5 V & 230 Vac) power consumption with no cable plug in
- Very low ripple and noise
- Inherent SCP and OCP protection
- High operation frequency up to 150kHz
- High power density (1.15 W/cm^3)
- Quick switching off FET while unplugging cable and switching on FET at Vbus dropping to 5 V while plugging cable again
- Quasi-Resonant current mode control with Valley Switching
- Valley lockout avoids audible noise at valley jumping operation
- Support TYPE-C PD3.0 & QC3.0 protocol
- Adaptive Output OVP and UVP
- Open loop protection
- Board size: 57mmx36mmx19mm

Block Diagram and BOARD Photos

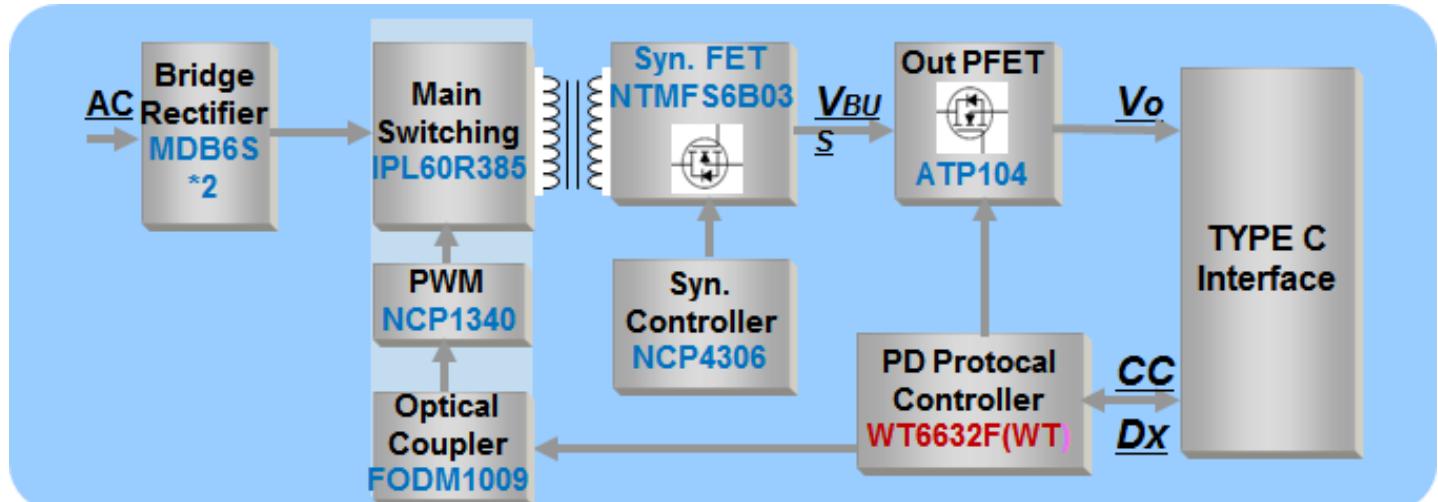


Figure 1, Overall cycle of 45 W TYPE-C PD Adapter Solution

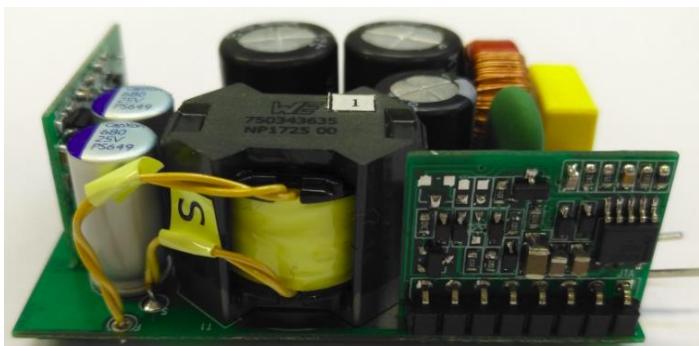


Figure 2, Side view 1 of demoboard

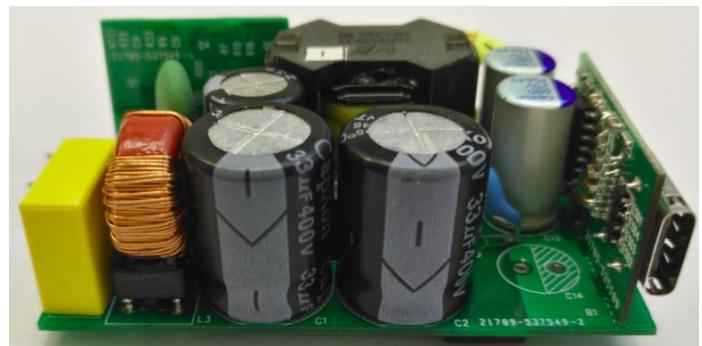
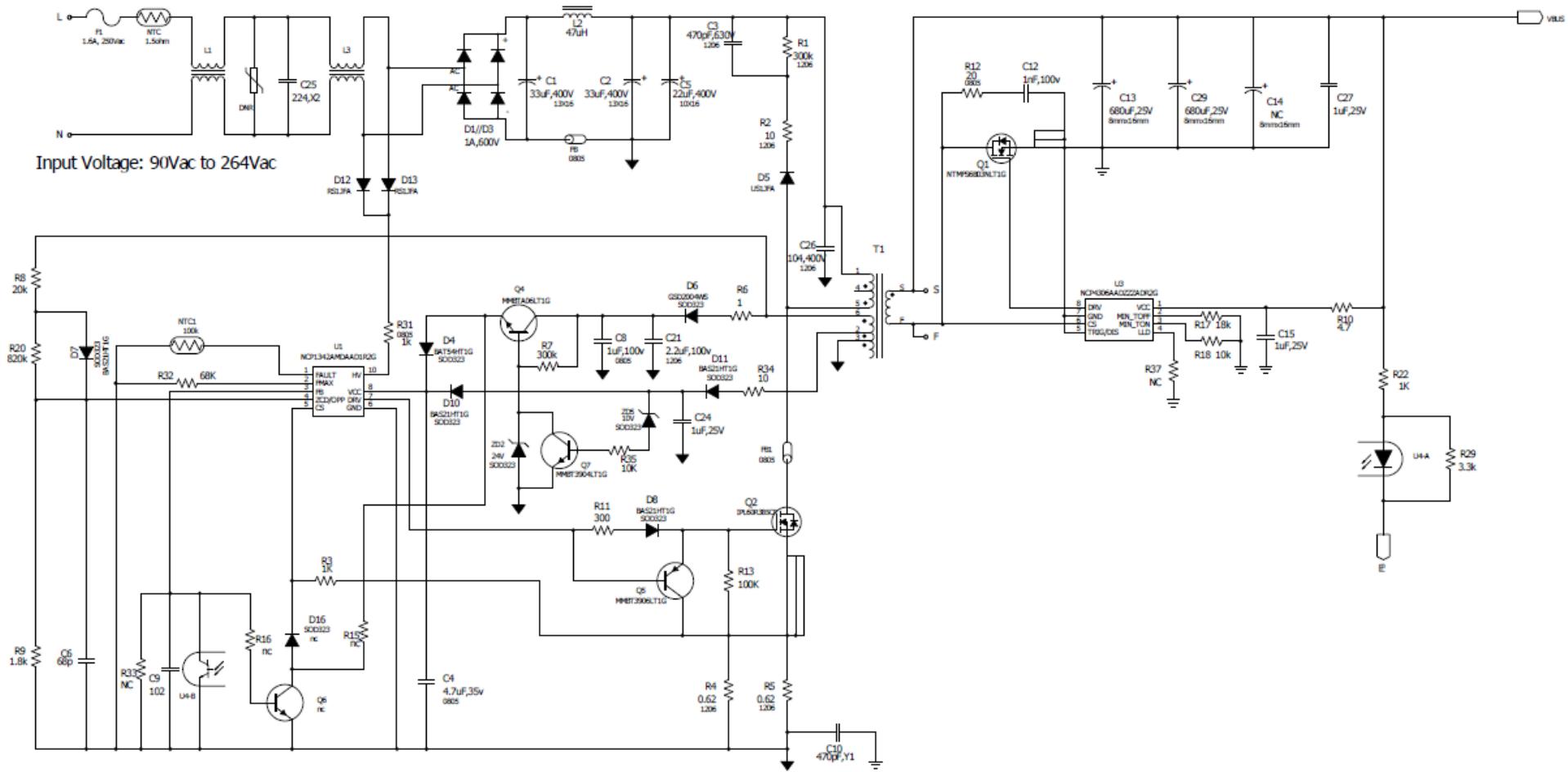
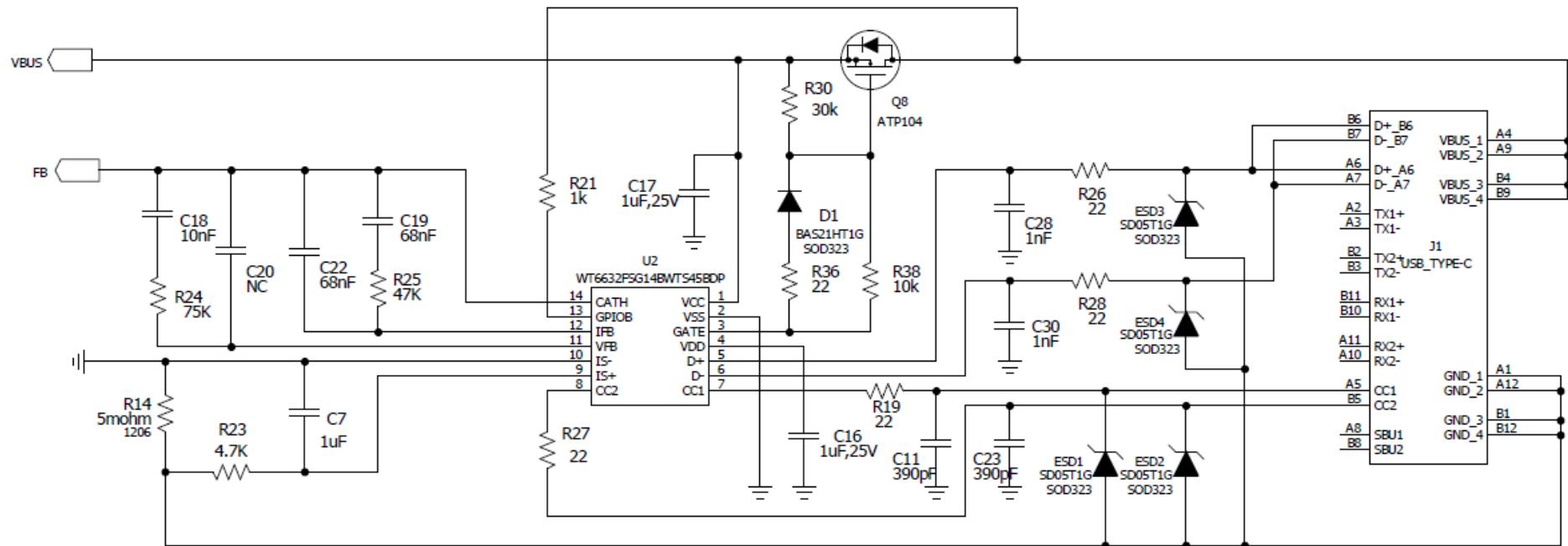


Figure 3, Side view 2 of demoboard

DN05104/D Circuit Schematic



DN05104/D
Circuit Schematic (Continued)



**DN05104/D
PCB**

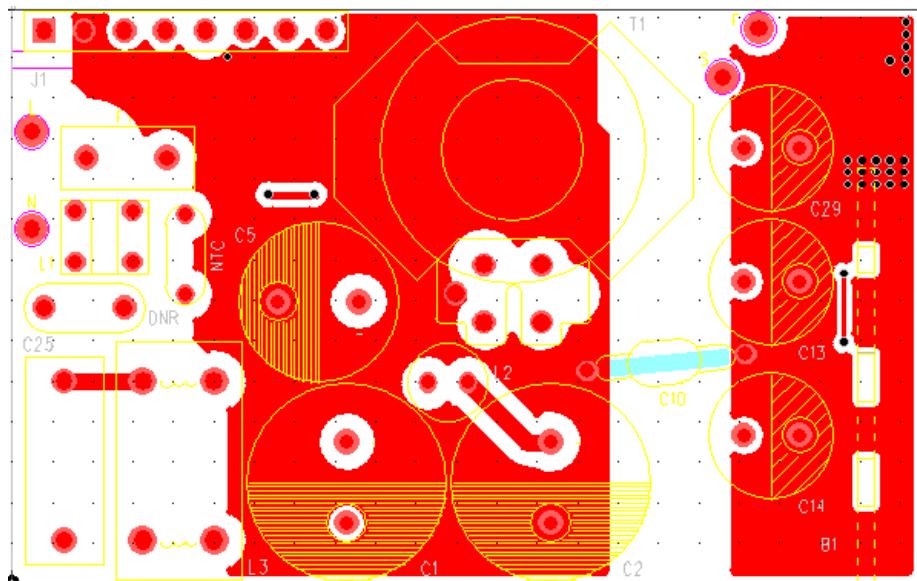


Figure 3, Top View of Mainboard's PCB

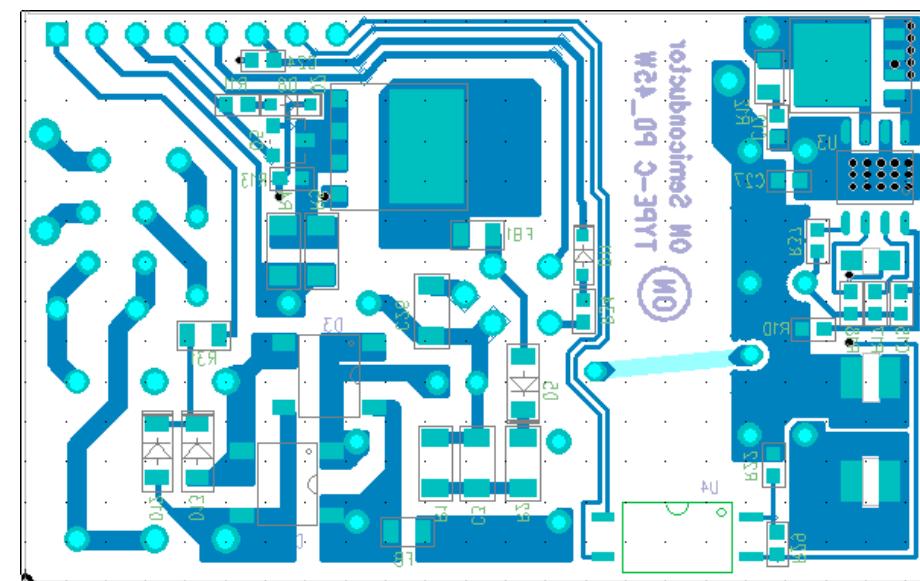


Figure 4, Bottom View of Mainboard's PCB

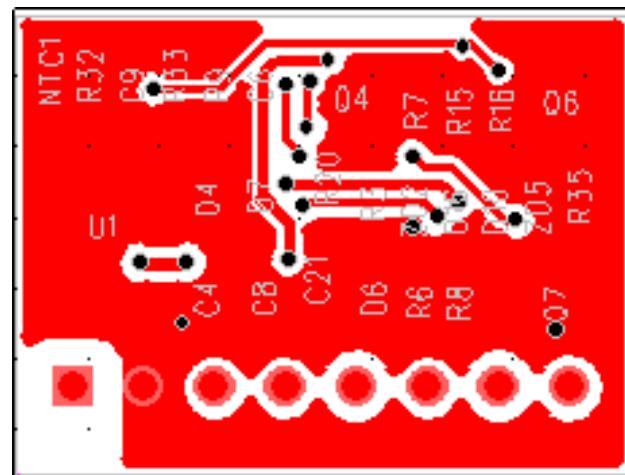


Figure 5, Top View of PWM control board's PCB

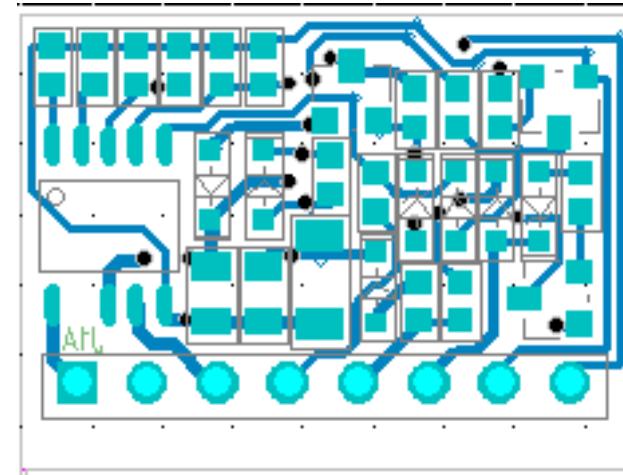


Figure 6, Bottom View of PWM control board's PCB

DN05104/D
PCB Layout(Cont'd)

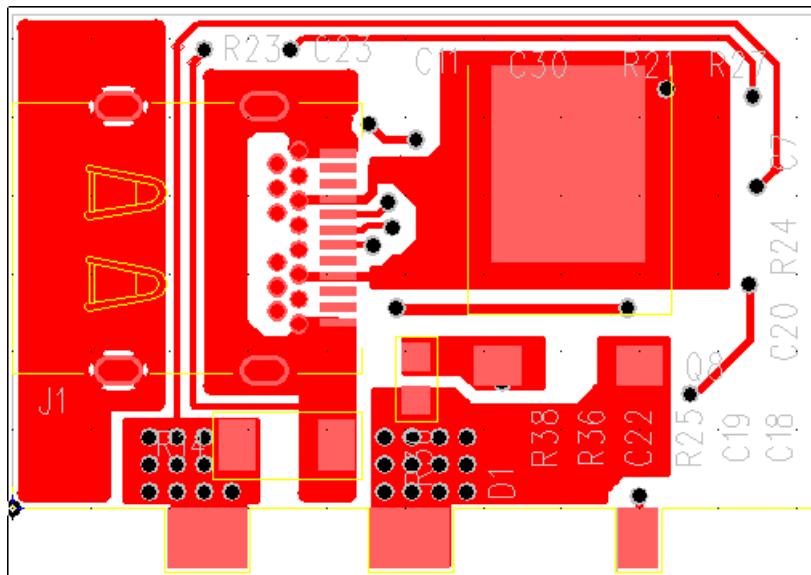


Figure 7, Top View of PD control board (WT6632F)'s PCB

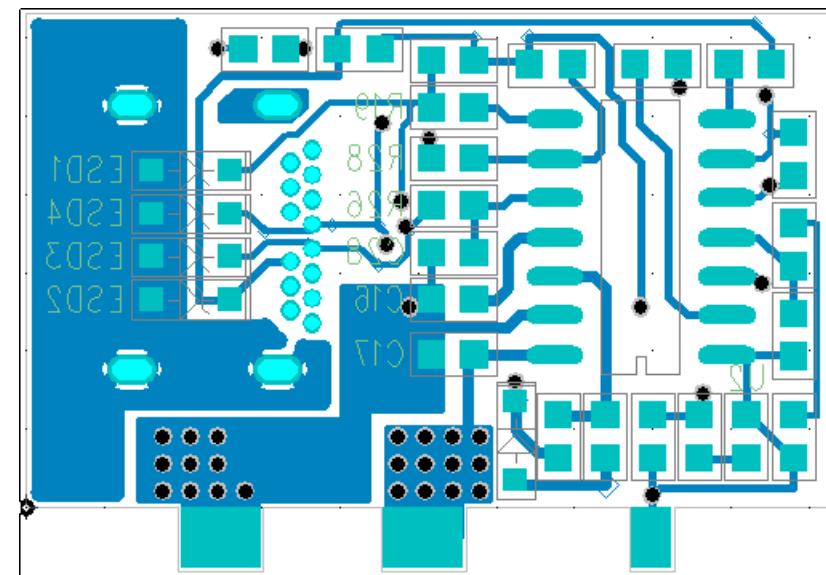


Figure 8, Bottom View of PD control board (WT6632F)'s PCB

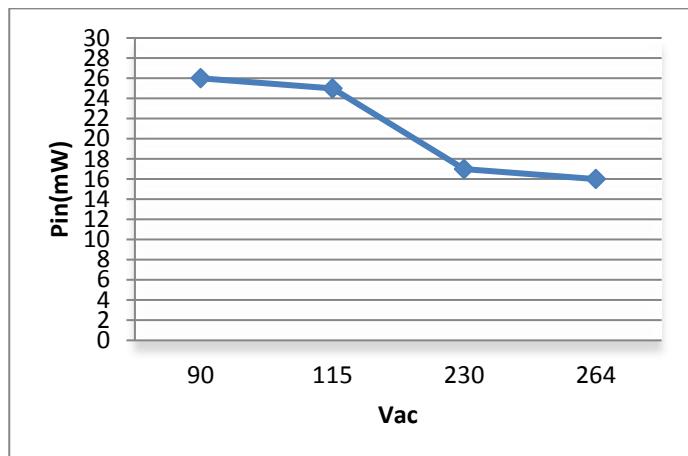
DN05104/D

T1 Transformer Designs (Available from Wurth Electronics)

CUSTOMER TERMINAL			RoHS	LEAD(Pb)-FREE																																								
Sn 96%, Ag 4%			Yes	Yes																																								
 ELECTRICAL SPECIFICATIONS @ 25°C unless otherwise noted: <table border="1" style="margin-top: 10px; border-collapse: collapse; width: 100%;"> <thead> <tr> <th style="text-align: center;">PARAMETER</th> <th style="text-align: center;">TEST CONDITIONS</th> <th style="text-align: center;">VALUE</th> </tr> </thead> <tbody> <tr> <td style="text-align: center;">D.C. RESISTANCE</td> <td style="text-align: center;">10-12</td> <td style="text-align: center;">@20°C</td> </tr> <tr> <td style="text-align: center;">D.C. RESISTANCE</td> <td style="text-align: center;">3-1</td> <td style="text-align: center;">@20°C</td> </tr> <tr> <td style="text-align: center;">D.C. RESISTANCE</td> <td style="text-align: center;">1-11</td> <td style="text-align: center;">@20°C</td> </tr> <tr> <td style="text-align: center;">D.C. RESISTANCE</td> <td style="text-align: center;">S-F</td> <td style="text-align: center;">@20°C</td> </tr> <tr> <td style="text-align: center;">INDUCTANCE</td> <td style="text-align: center;">10-12</td> <td style="text-align: center;">10kHz, 1V, Ls</td> </tr> <tr> <td style="text-align: center;">SATURATION CURRENT</td> <td style="text-align: center;">10-12</td> <td style="text-align: center;">20% rolloff from initial</td> </tr> <tr> <td style="text-align: center;">LEAKAGE INDUCTANCE</td> <td style="text-align: center;">10-12</td> <td style="text-align: center;">8e(1+3+10+S+F), 100kHz, 1V, Ls</td> </tr> <tr> <td style="text-align: center;">DIELECTRIC</td> <td style="text-align: center;">1-8</td> <td style="text-align: center;">8e(1+2+3+10+11+12), 3750VAC, 1 second</td> </tr> <tr> <td style="text-align: center;">DIELECTRIC</td> <td style="text-align: center;">S-CORE</td> <td style="text-align: center;">3750VAC, 1 second</td> </tr> <tr> <td style="text-align: center;">TURNS RATIO</td> <td style="text-align: center;">(10-12):(3-1)</td> <td style="text-align: center;">3.25:1, ±2%</td> </tr> <tr> <td style="text-align: center;">TURNS RATIO</td> <td style="text-align: center;">(10-12):(1-11)</td> <td style="text-align: center;">6.5:1, ±2%</td> </tr> <tr> <td style="text-align: center;">TURNS RATIO</td> <td style="text-align: center;">(10-12):(S-F)</td> <td style="text-align: center;">6.5:1, ±2%</td> </tr> </tbody> </table>					PARAMETER	TEST CONDITIONS	VALUE	D.C. RESISTANCE	10-12	@20°C	D.C. RESISTANCE	3-1	@20°C	D.C. RESISTANCE	1-11	@20°C	D.C. RESISTANCE	S-F	@20°C	INDUCTANCE	10-12	10kHz, 1V, Ls	SATURATION CURRENT	10-12	20% rolloff from initial	LEAKAGE INDUCTANCE	10-12	8e(1+3+10+S+F), 100kHz, 1V, Ls	DIELECTRIC	1-8	8e(1+2+3+10+11+12), 3750VAC, 1 second	DIELECTRIC	S-CORE	3750VAC, 1 second	TURNS RATIO	(10-12):(3-1)	3.25:1, ±2%	TURNS RATIO	(10-12):(1-11)	6.5:1, ±2%	TURNS RATIO	(10-12):(S-F)	6.5:1, ±2%	
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GENERAL SPECIFICATIONS: OPERATING TEMPERATURE RANGE: -40°C to +125°C including temp rise. Designed to comply with the following requirements as defined by IEC60065-1, EN60065-1, UL60065-1/CSA60065-1 and AS/NZS60065.1: - Reinforced insulation for a primary circuit at a working voltage of 265Vrms, 400Vpeak, Overvoltage Category II.																																												
Wire insulation & RoHS status not affected by wire color. Wire insulation color may vary depending on availability.																																												
DFM	Packaging Specifications		Tolerances unless otherwise specified: Angles: ±1° Decimals: ±.005 [.13] Fractions: ±1/64 Footprint: ± .001 [.03]		DRAWING TITLE TRANSFORMER	PART NO.																																						
DATE	 Method: Tray PKG-TBD		 CONVENTION PLACEMENT		This drawing is dual dimensioned. Dimensions in brackets are in millimeters.	750343635																																						
ENG							HWE																																					
REV.	00																																											
DATE	6/30/2017					SPECIFICATION SHEET 1 OF 1																																						

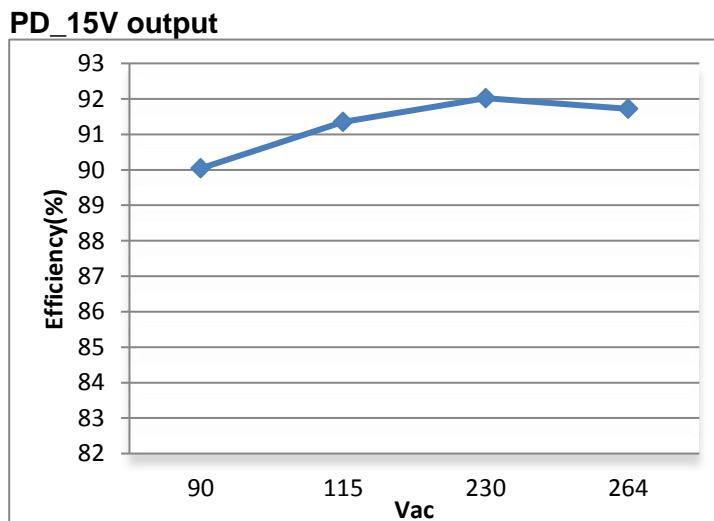
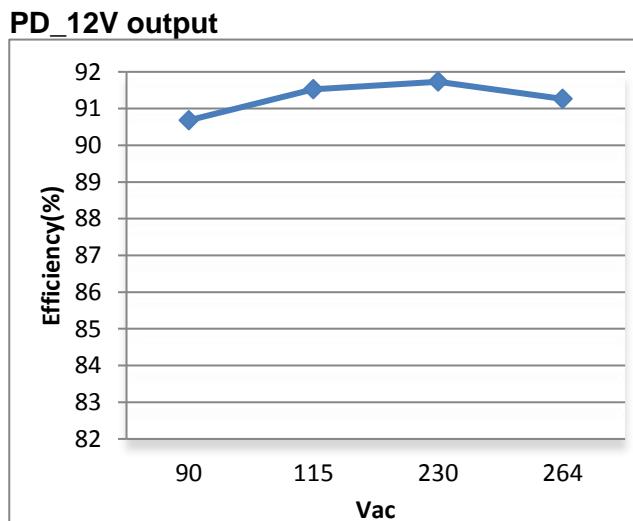
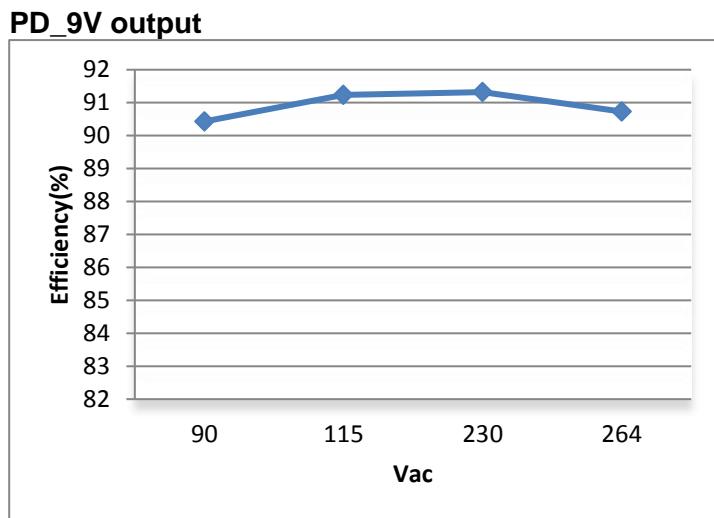
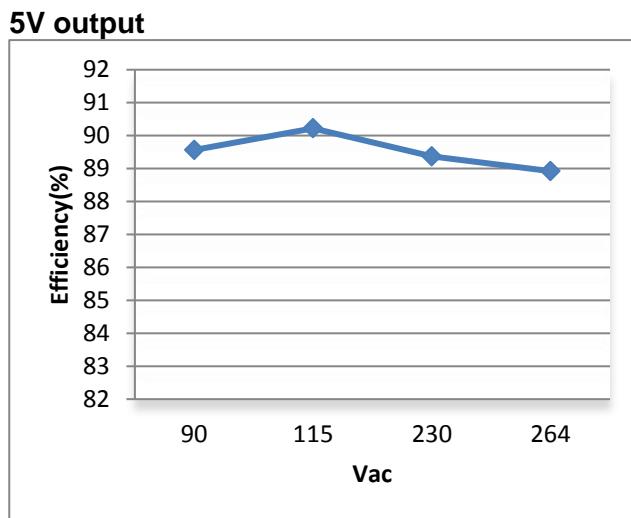
Standby Power at 5V Output (Cable unplug) @ 90 Vac to 264 Vac Input

Test condition: all efficiency are tested at board end



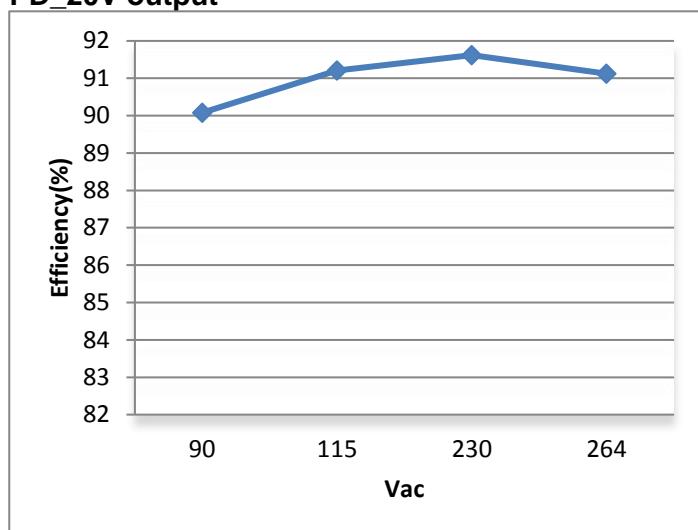
Average Efficiency

Test condition: all efficiency are tested at board end

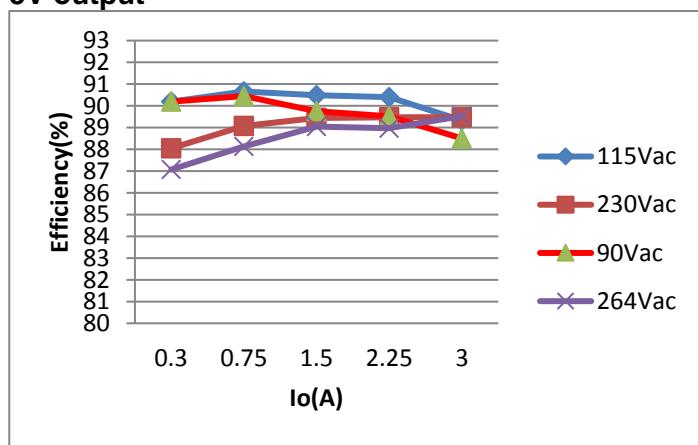
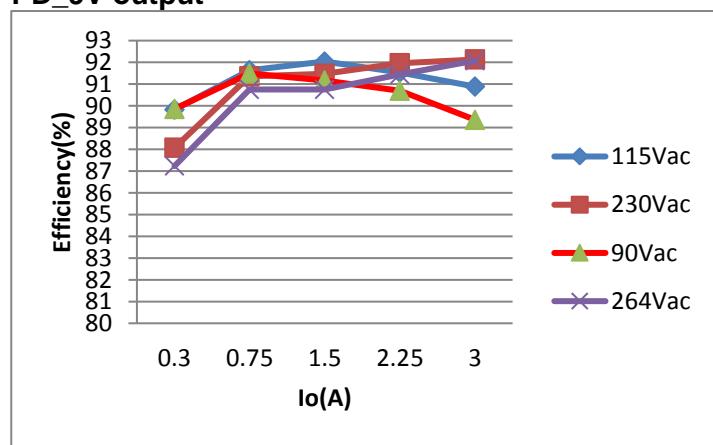
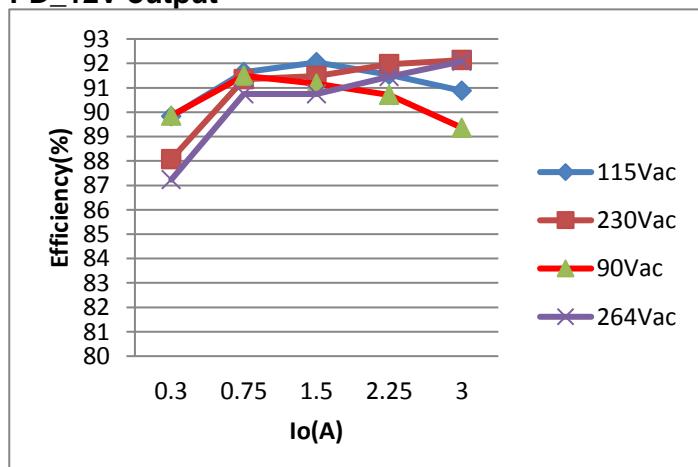
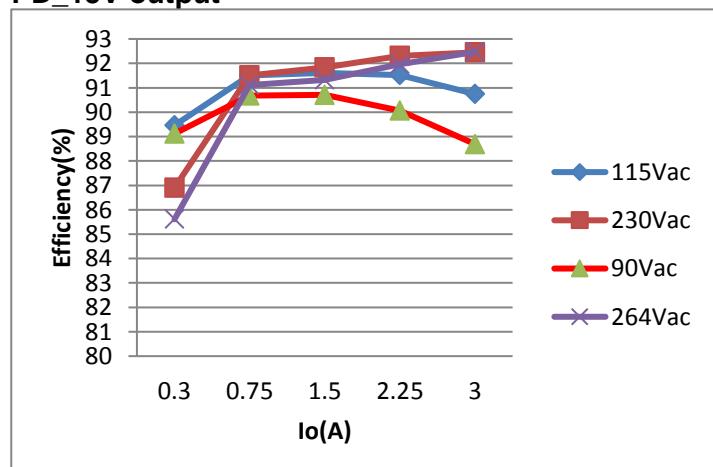


Average Efficiency (Continued)

Test condition: all efficiency are tested at board end

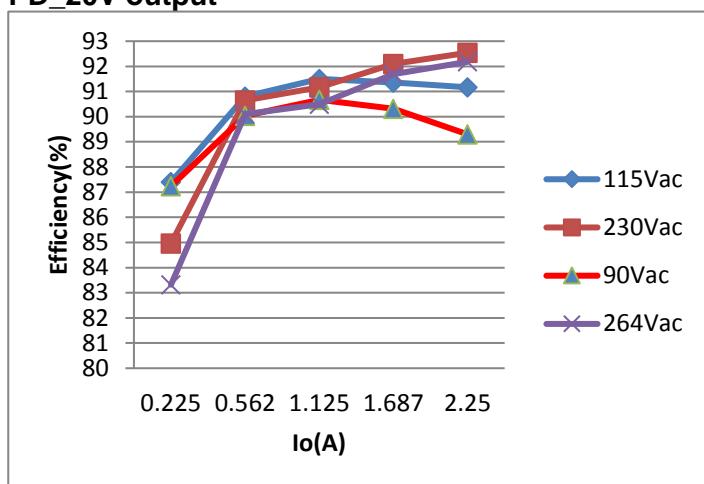
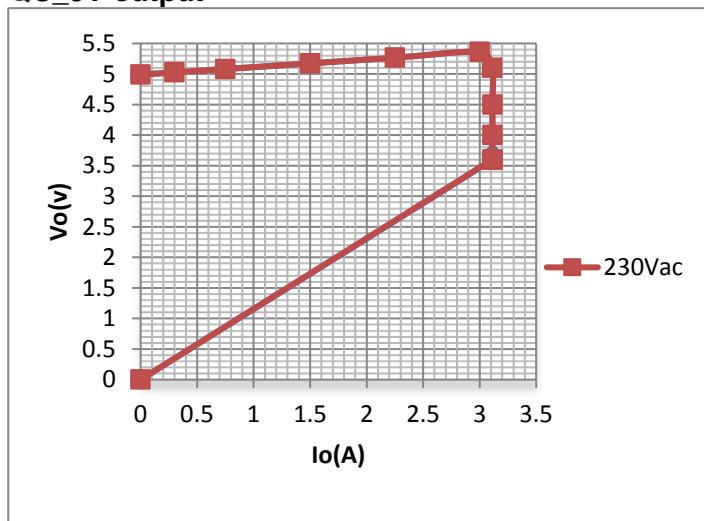
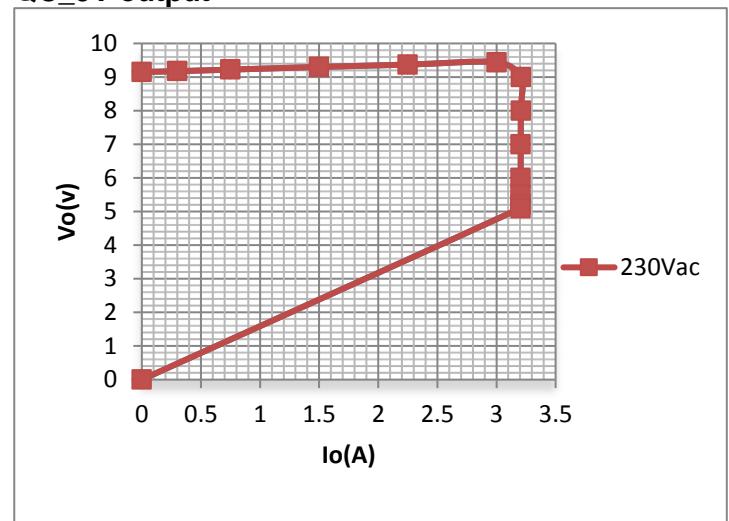
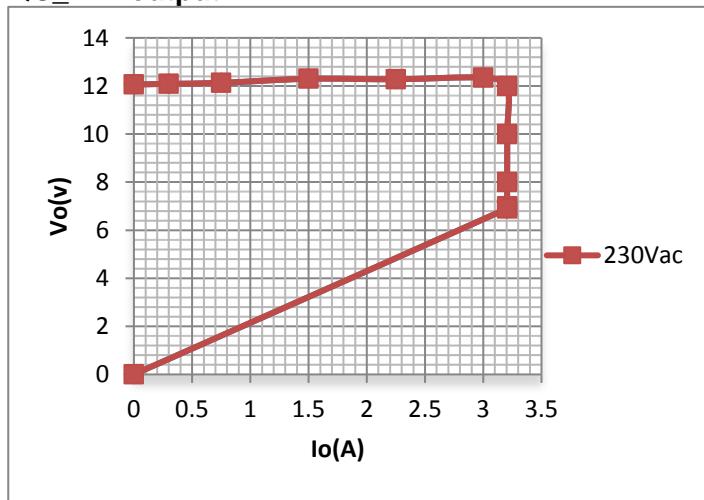
PD_20V output**Efficiency vs Output Load Curves**

Test condition: all efficiency are tested at board end

5V output**PD_9V output****PD_12V output****PD_15V output**

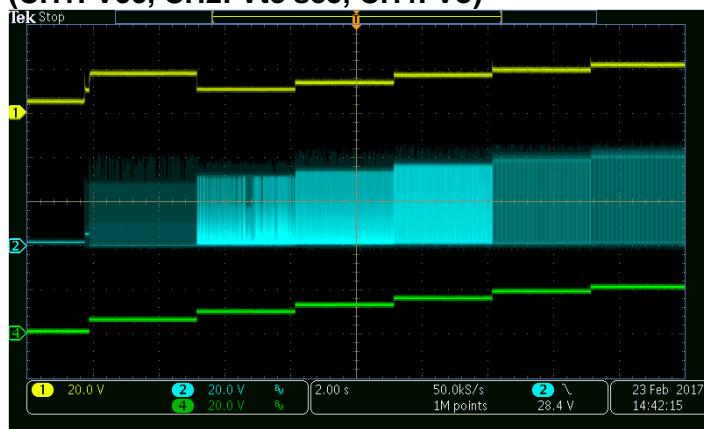
Efficiency vs Output Load Curves(Continued)

Test condition: all efficiency are tested at board end

PD_20V output**I-V Curves****QC_5V output****QC_9V output****QC_12V output**

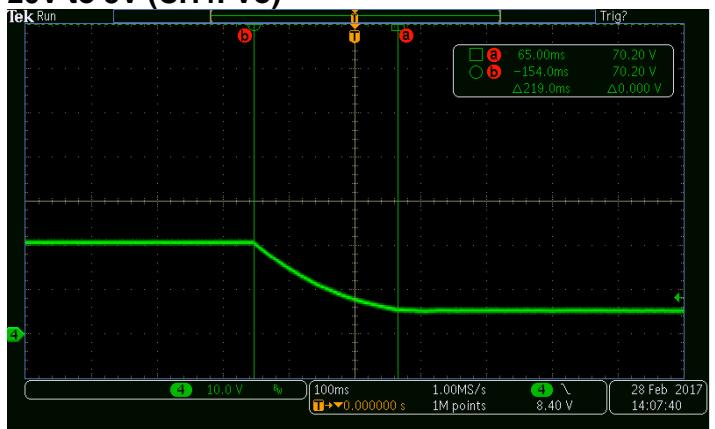
Power On and PD Volatge Change

(CH1: Vcc, CH2: Vte sec, CH4: Vo)



PD Transition with PD Emulator

20V to 5V (CH4: Vo)



Discharge Time @ Unplug cable

PD (20V to 5V)

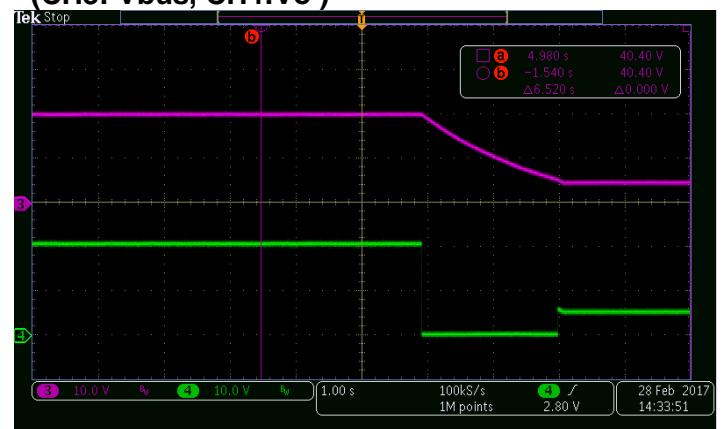
(CH1: Vcc, CH2:Vsyn_FET, CH3:Vbus, CH4:Vo)



Quick Unplug/Plug Cable

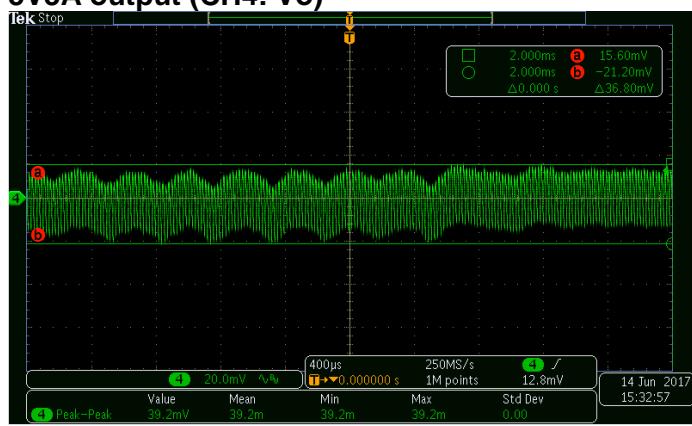
PD_15V output

(CH3: Vbus, CH4:Vo)

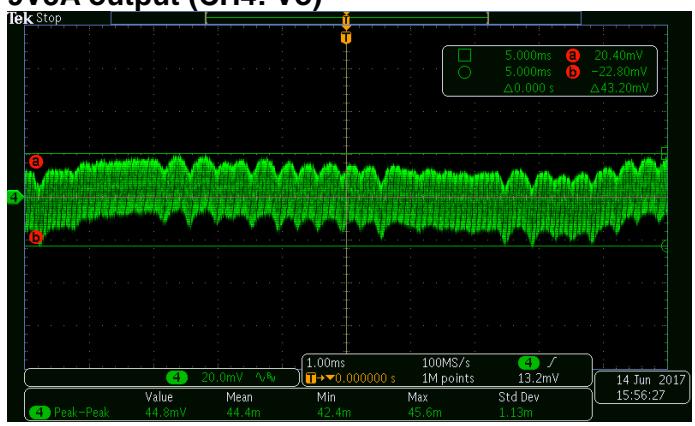


Output Ripple @ 90 Vac Input, 3A Output

5V3A output (CH4: Vo)

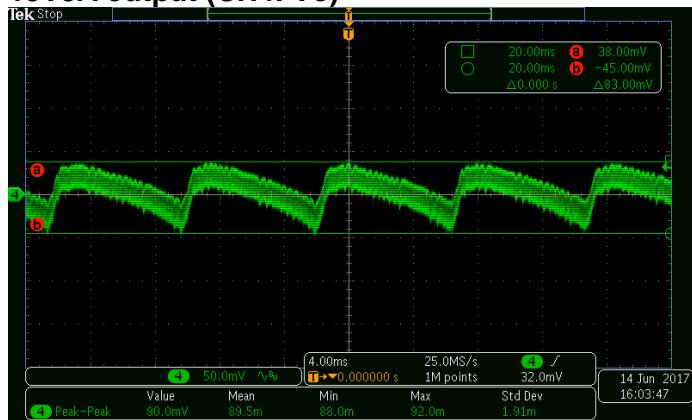


9V3A output (CH4: Vo)

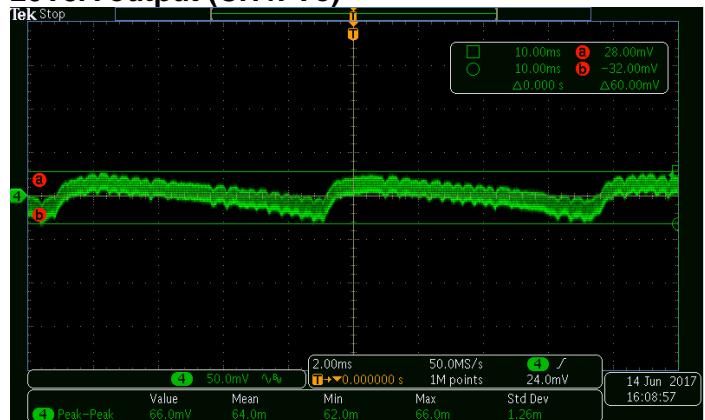


Output Ripple @ 90 Vac Input, 3A Output (Continued)

15V3A output (CH4: Vo)

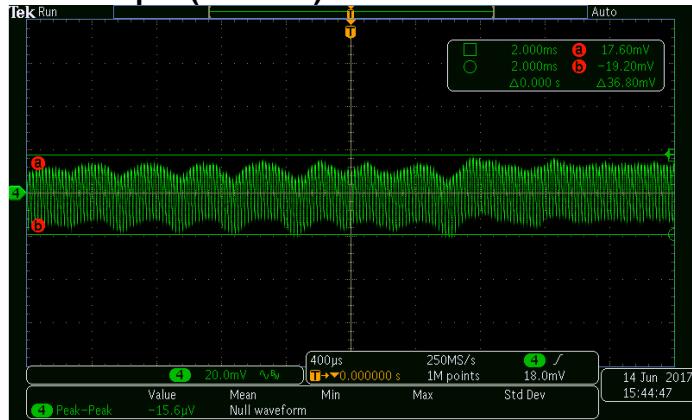


20V3A output (CH4: Vo)

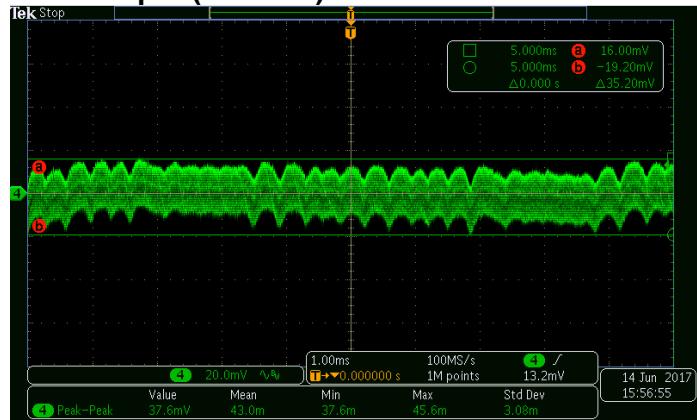


Output Ripple @ 115 Vac Input, 3A Output

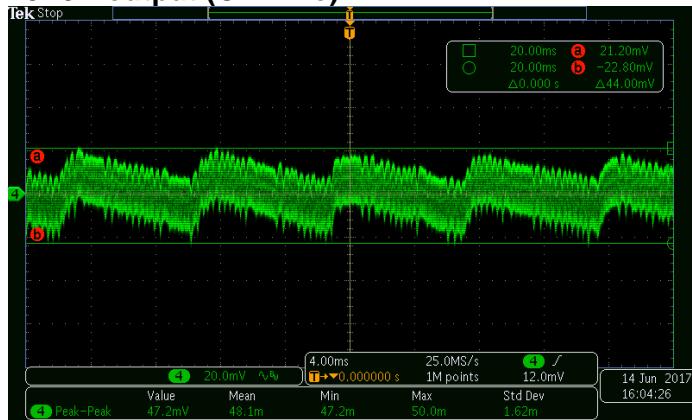
5V3A output (CH4: Vo)



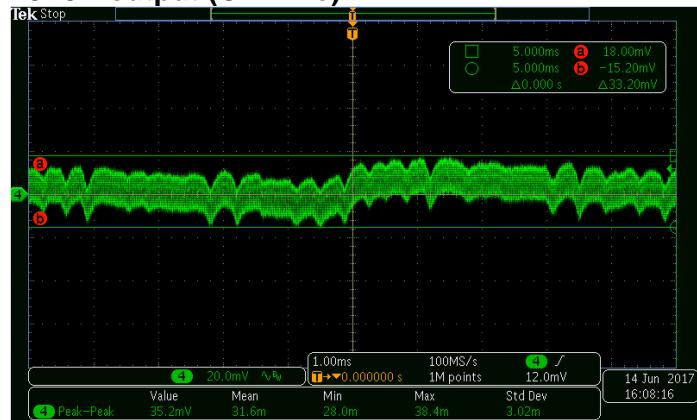
9V3A output (CH4: Vo)



15V3A output (CH4: Vo)

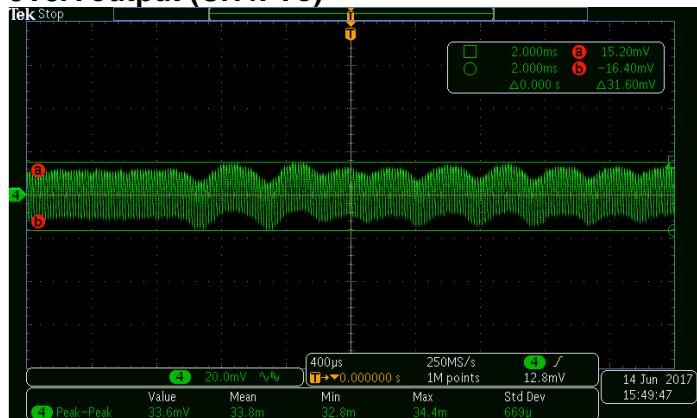


20V3A output (CH4: Vo)

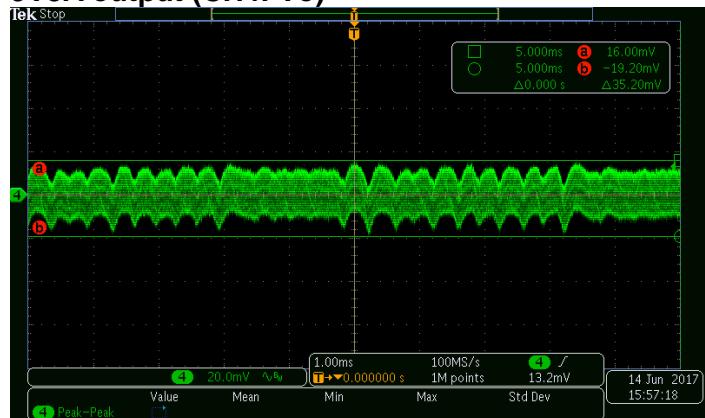


Output Ripple @ 230 Vac Input, 3A Output

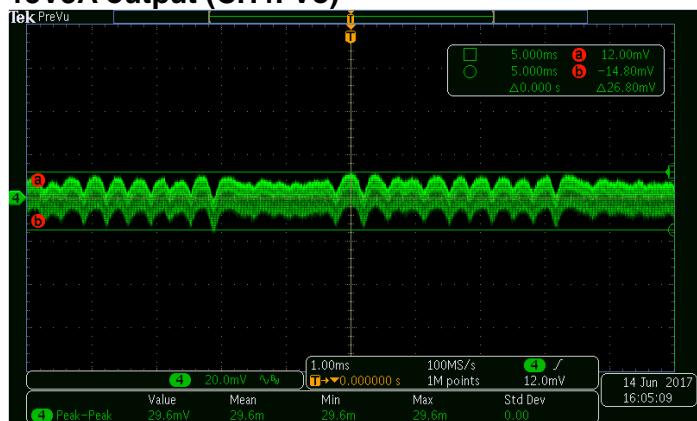
5V3A output (CH4: Vo)



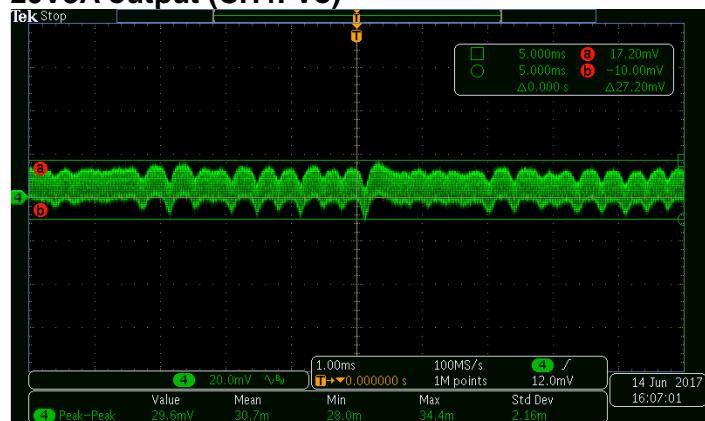
9V3A output (CH4: Vo)



15V3A output (CH4: Vo)

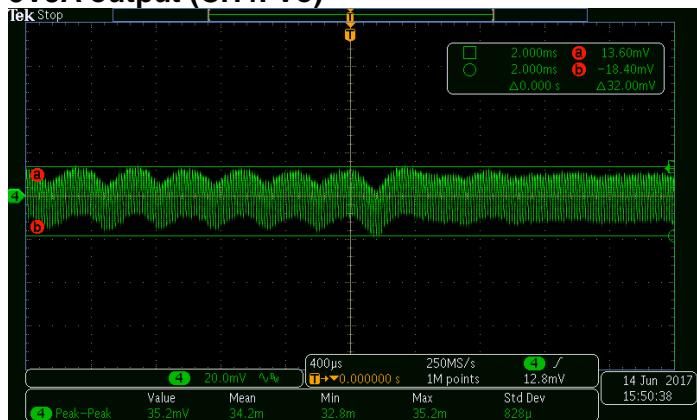


20V3A output (CH4: Vo)

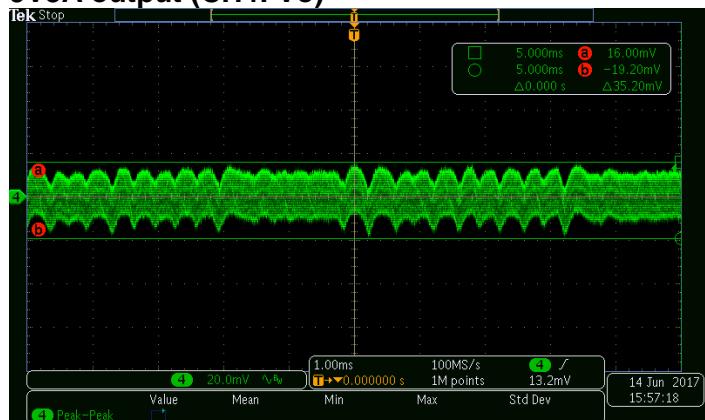


Output Ripple @ 264 Vac Input, 3A Output

5V3A output (CH4: Vo)

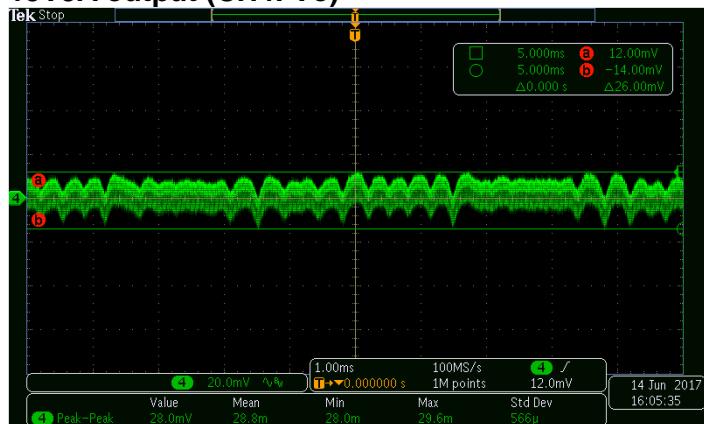


9V3A output (CH4: Vo)

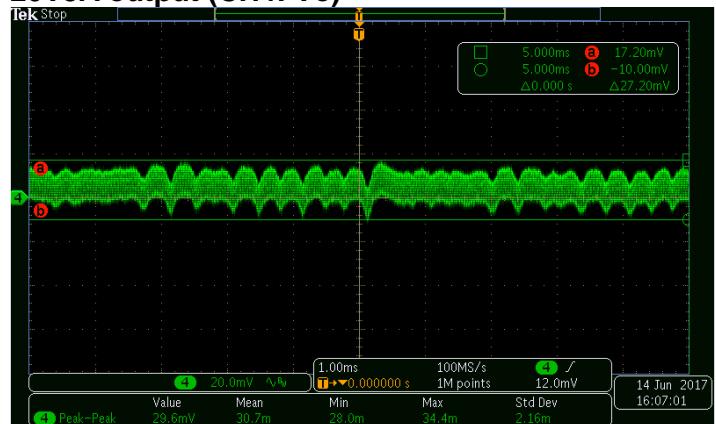


Output Ripple @ 264 Vac Input, 3A Output (Continued)

15V3A output (CH4: Vo)

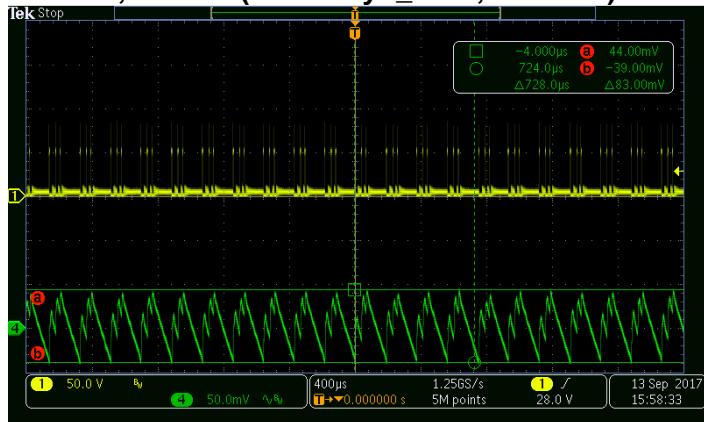


20V3A output (CH4: Vo)

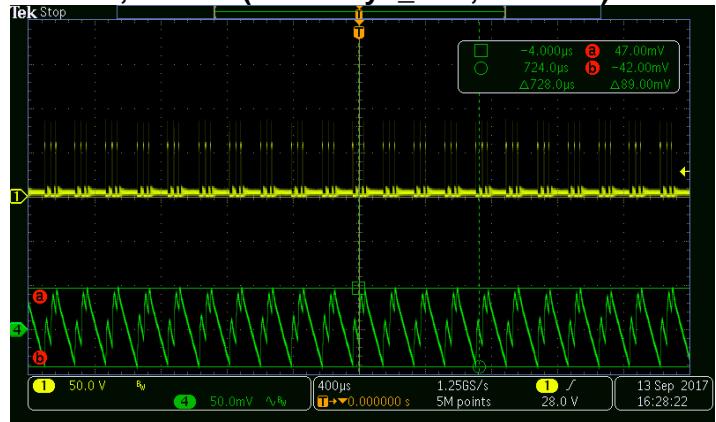


Output Ripple @ High Line & Light Load

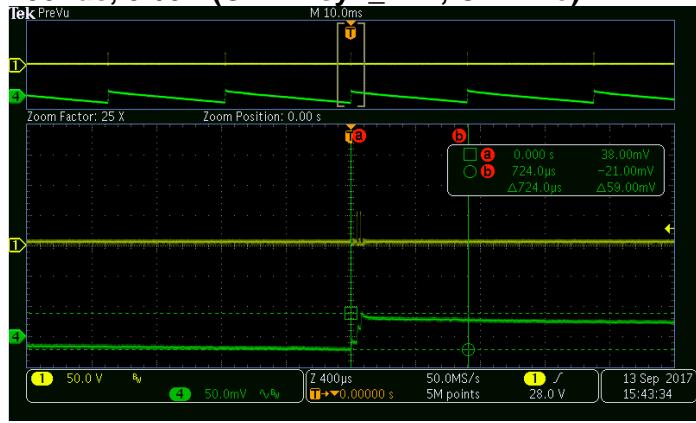
230Vac, 5V/0.8A(CH1: Vsyn_FET , CH4: Vo)



264Vac, 5V/0.9A(CH1: Vsyn_FET, CH4: Vo)

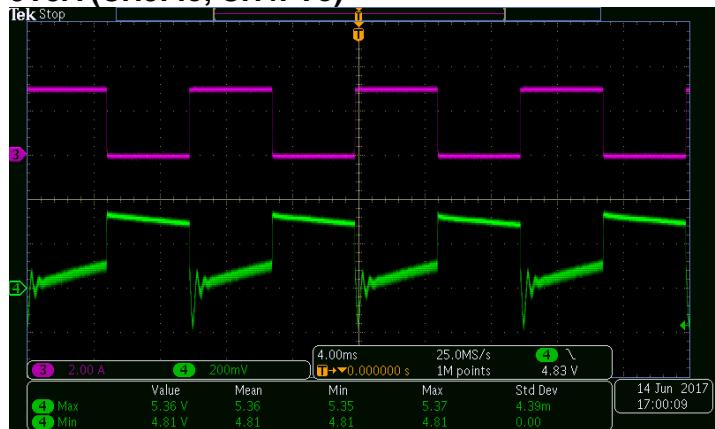


230Vac, 5v/0A (CH1: Vsyn_FET, CH4: Vo)



Dynamic Test @ 115 Vac Input

5V3A (CH3: Io, CH4: Vo)



9V3A (CH3: Io, CH4: Vo)



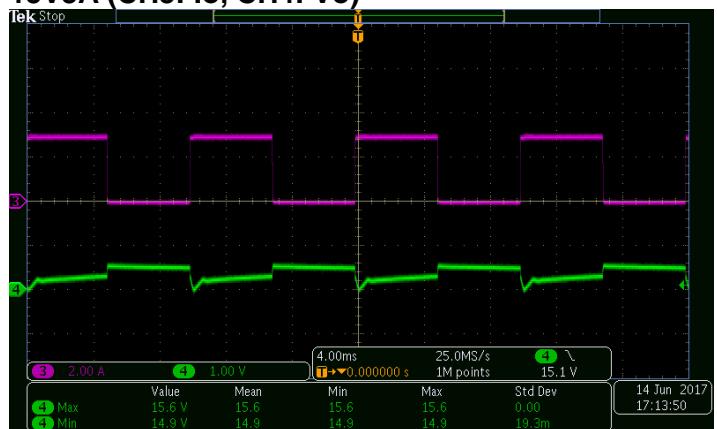
Test condition: 0-3A, 10mS cycle, 125mA/us
1m cable, tested at E-load

12V3A (CH3: Io, CH4: Vo)



Test condition: 0-3A, 10mS cycle, 125mA/us
1m cable, tested at E-load

15V3A (CH3: Io, CH4: Vo)



Test condition: 0-3A, 10mS cycle, 125mA/us
1m cable, tested at E-load

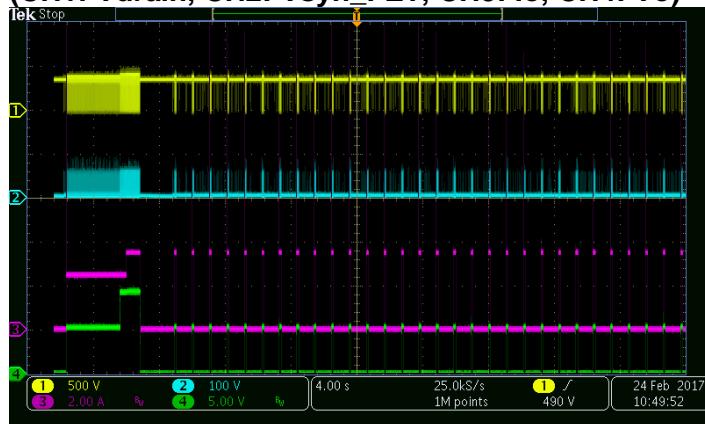
20V2.25A (CH3: Io, CH4: Vo)



Test condition: 0-2.25A, 10mS cycle, 125mA/us
1m cable, tested at E-load

OCP @ 264 Vac Input, 9 Vdc Output

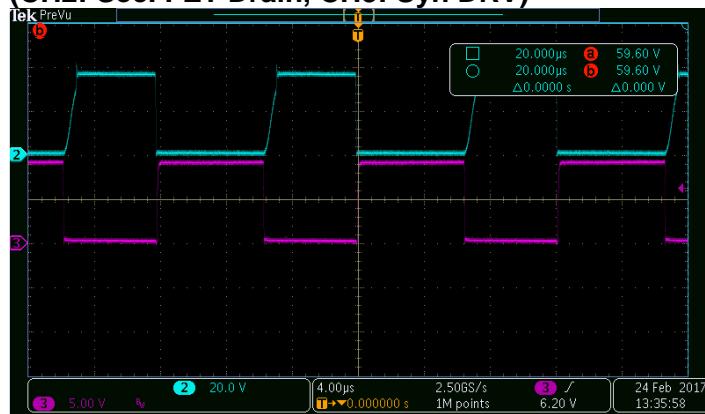
(CH1: Vdrain, CH2: Vsyn_FET, CH3: Io, CH4: Vo)



Synchronous Drive

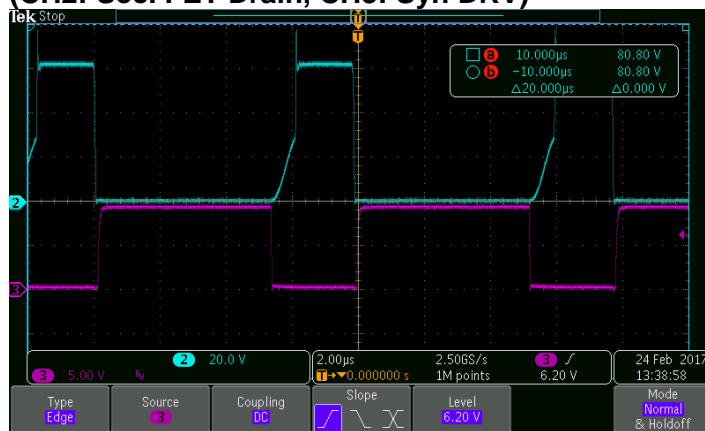
115 Vac input, 15V3A output

(CH2: Sec. FET Drain, CH3: Syn DRV)



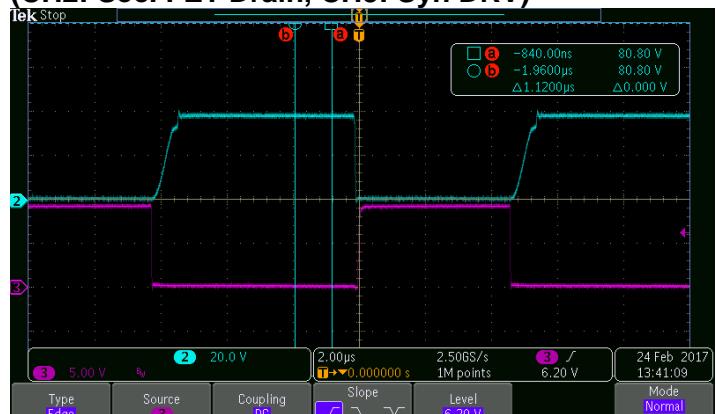
230 Vac input, 15V3A output

(CH2: Sec. FET Drain, CH3: Syn DRV)



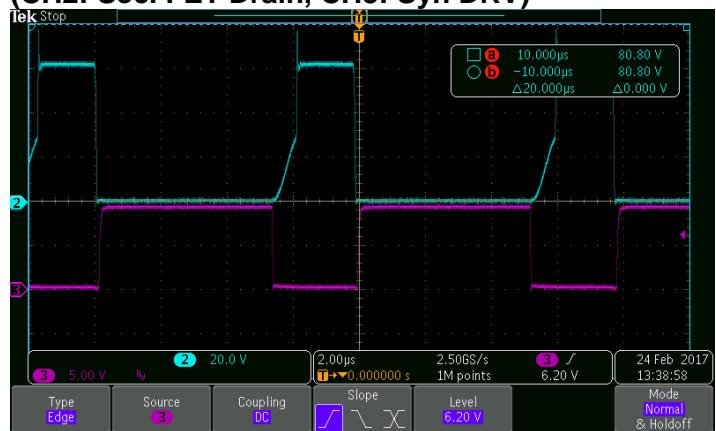
115 Vac input, 20V2.25A output

(CH2: Sec. FET Drain, CH3: Syn DRV)



230 Vac input, 20V2.25A output

(CH2: Sec. FET Drain, CH3: Syn DRV)



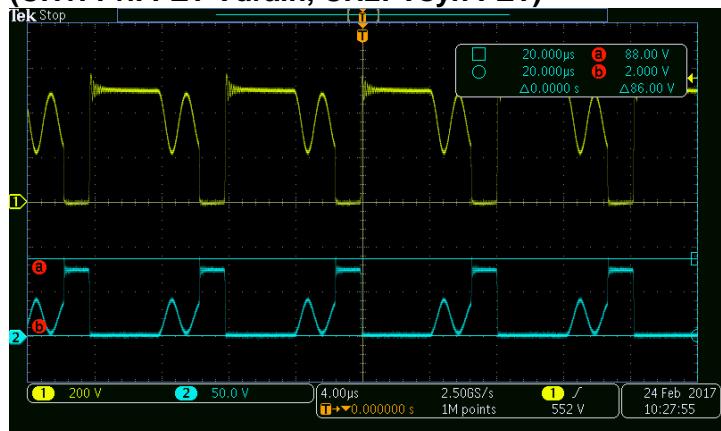
Primary FET Drain Voltage @ 264 Vax input, 20V2.25A output

(CH1: Pri. FET V_{drain}, CH2: V_{syn} FET)



Synchronic FET Drain Voltage @ 264 Vax input, 20V2.25A output

(CH1: Pri. FET V_{drain}, CH2: V_{syn} FET)



Thermal Image @ 20V2.25A Output

Input	Component Side	Back side
90 Vac	<p>FLUKE 93.4°C 自动 2 106.1</p> <p>最大 101.4 最小 25.8 高 89.2 ε=0.95 BG=22.0 τ=100% 9/14/17 10:16:16 AM</p>	<p>FLUKE 81.8°C 自动 2 106.1</p> <p>最大 105.2 最小 26.3 高 87.3 ε=0.95 BG=22.0 τ=100% 9/14/17 10:07:49 AM</p>
115 Vac	<p>FLUKE 84.8°C 自动 2 89.4</p> <p>最大 88.5 最小 25.8 高 43.4 ε=0.95 BG=22.0 τ=100% 9/14/17 10:28:05 AM</p>	<p>FLUKE 69.5°C 自动 2 94.0</p> <p>最大 93.7 最小 26.0 高 79.8 ε=0.95 BG=22.0 τ=100% 9/14/17 10:28:34 AM</p>
230 Vac	<p>FLUKE 85.7°C 自动 2 90.1</p> <p>最大 89.2 最小 25.8 高 62.1 ε=0.95 BG=22.0 τ=100% 9/14/17 10:37:42 AM</p>	<p>FLUKE 78.1°C 自动 2 97.2</p> <p>最大 98.0 最小 26.5 高 69.7 ε=0.95 BG=22.0 τ=100% 9/14/17 10:37:17 AM</p>
264 Vac	<p>FLUKE 82.0°C 自动 2 87.3</p> <p>最大 85.5 最小 21.2 高 54.2 ε=0.95 BG=22.0 τ=100% 9/14/17 10:57:42 AM</p>	<p>FLUKE 90.4°C 自动 2 100.6</p> <p>最大 100.8 最小 24.7 高 67.6 ε=0.95 BG=22.0 τ=100% 9/14/17 10:58:42 AM</p>

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BOM

Item	Qty	Reference	Type	Part Name	MFR	Value	Package	Description
1	1	C9	Ceramic Capacitor	/885012207116	WE	102	603	Capacitor, Ceramic, 50V, 10%
2	1	C26	Ceramic Capacitor	C3216X7T2W104K	TDK	104, 400V	1206	Capacitor, Ceramic, SMD, 5%
3	1	C18	Ceramic Capacitor	/885012006051	WE	10nF	603	Capacitor, Ceramic, 50V, 10%
4	2	C28 C30	Ceramic Capacitor	/885012206083	WE	1nF	603	Capacitor, Ceramic, 50V, 10%
5	1	C12	Ceramic Capacitor	C1608C0G2A102J	TDK	1nF, 100v	603	Capacitor, Ceramic, SMD, 5%
6	1	C7	Ceramic Capacitor	/885012206076	WE	1uF, 25v	603	Capacitor, Ceramic, 25V, 10%
7	1	C8	Ceramic Capacitor	C2012X7S2A105K	TDK	1uF, 100v	805	Capacitor, Ceramic, 100V, 10%
8	5	C15-17 C24 C2	Ceramic Capacitor	/885012206076	WE	1uF, 25V	603	Capacitor, Ceramic, 25V, 10%
9	1	C21	Ceramic Capacitor	C3216X7S2A225K	TDK	2. 2uF, 100v	1206	Capacitor, Ceramic, 100V, 10%
10	1	C25	X2 Capacitor	/890324023028	WE	224, X2	THT, 10m	X2 capacitor, Safety standard approved, 10
11	2	C11 C23	Ceramic Capacitor	std	std	390pF	603	Capacitor, Ceramic, 50V, 10%
12	1	C4	Ceramic Capacitor	C2012X7R1V475K	TDK	4. 7uF, 35v	805	Capacitor, Ceramic, 35V, 10%
13	1	C3	Ceramic Capacitor	C3216C0G2J471J	TDK	470pF, 630V	1206	Capacitor, Ceramic, Chip, 5%
14	1	C10	Ceramic Capacitor	CS65-B2GA101KYN	TDK	470pF, Y1	ead type	HV Ceramic Capacitor, safety standard appro
15	2	C19 C22	Ceramic Capacitor	/885012206094	WE	68nF	603	Capacitor, Ceramic, 50V, 10%
16	1	C6	Ceramic Capacitor	/885012006056	WE	68pF	603	Capacitor, Ceramic, 50V, 5%
17	1	C20	Ceramic Capacitor	Std	std	NC	603	Capacitor, Ceramic, 50V, 10%
18	2	D1 D3	Bridge rectifier	MDB6S	FSC	1A, 600V	icro-DIP	Bridge Rectifier, 600V, 1A
19	1	DNR	Varistor	820573011	WE	10D471K	TH	Varistor, 10D471K
20	4	D1 D7 D10-11	Switching diode	BAS21HT1G	ON	0. 2A, 250V	SOD323	Switching diode, SMD
21	1	D16	Switching diode	NC	ON	0. 2A, 250V	SOD323	NC
22	1	D6	Switching diode	GSD2004WS	Vishay	0. 2A, 300V	SOD323	Switching diode, SMD
23	1	D4	Switching diode	BAT54HT1G	ON	0. 2A, 30V	SOD323	Switching diode, SMD
24	1	D5	Ultrafast rectifier	US1JFA	ON(FSC)	0. 8A, 600V	SOD123FL	Standard Rectifier, 0. 8A, 600V
25	2	D12-13	Standard rectifier	RS1JFA	ON(FSC)	0. 8A, 600V	SOD123FL	Standard Rectifier, 0. 8A, 600V
26	1	D8	Switching diode	BAS21HT1G	ON	0. 2A, 250V	SOD323	Switching diode, SMD
27	1	FB	Ferrite bead	UPZ2012E102-1R5	Sunlord/Wueth		805	1000ohm@100MHz
28	1	FB1	Ferrite bead	UPZ2012E601-2R0	Sunlord/Wueth		805	600ohm@100MHz
29	1	L3	Common filter	744821110	WE	10mH	TH type	CM Filter, T type core
30	1	L1	Common filter	150-1327	Wurth-M	500uH	TH type	T type, 6. 3x3x3, 11T, 0. 2mmx2 in parallel
31	1	F1	Fuse	20T-016H	Hollyfu	1. 6A, 250V	ial lead	Micro Fuse, 1. 6A/250V
32	1	Q4	NPN Transistor	MMBTA06LT1G	ON		SOT23	General NPN Transistor, SMD
33	1	Q6	NPN Transistor	NC	ON		SOT23	NC
34	1	Q7	NPN Transistor	MMBT3904LT1G	ON		SOT23	General NPN Transistor, SMD
35	1	Q5	PNP Transistor	MMBT3906LT1G	ON		SOT23	General PNP Transistor, SMD
36	1	U3	Syn. rectified co	NCP4306AADZZADI	ON		S08	Syn. Rectified Controller

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BOM (Continued)

Item	Qty	Reference	Type	Part Name	MFR	Value	Package	Description
37	1	U1	PWM Controller	NCP1342AMDAAD1R2ON			SOP9	QR PWM controller
38	1	NTC	NTC	SPNL09D1R5MBI	Sunlord	1.5ohm	Lead type	9mm Die, 1.5ohm
39	1	NTC1	NTC	SDNT1608X104J425	Sunlord	100k	603	NTC, SMD
40	1	U4	Optical coupler	FODM1009	ON(FSC)		LSOP4	optical coupler, standard SOP package
41	1	Q8	PMOS	ATP104	ON	8.4mohm	ATPAK	PMOS
42	1	L2	Axial leaded fixe	7447462470	WE	47uH	TH type	Axial leaded fixed inductor
43	1	Q2	MOSFET	IPL60R385CP	Infineon		THINKPAK-8X8	MOSFET, NChan, 600V
44	1	R6	Resistor	Std	Std	1	603	Resistor, Chip, 1/8W, 1%
45	1	R9	Resistor	Std	Std	1.8k	603	Resistor, Chip, 1/8W, 1%
46	1	R34	Resistor	Std	Std	10	603	Resistor, Chip, 1/8W, 1%
47	1	R13	Resistor	Std	Std	100K	603	Resistor, Chip, 1/8W, 1%
48	3	R18 R35 R38	Resistor	Std	Std	10k	603	Resistor, Chip, 1/8W, 1%
49	1	R17	Resistor	Std	Std	18k	603	Resistor, Chip, 1/8W, 1%
50	3	R3 R21 R22	Resistor	Std	Std	1K	603	Resistor, Chip, 1/8W, 1%
51	1	R8	Resistor	Std	Std	20k	603	Resistor, Chip, 1/8W, 1%
52	5	R19 R26-28 R3	Resistor	Std	Std	22	603	Resistor, Chip, 1/8W, 1%
53	1	R29	Resistor	Std	Std	3.3k	603	Resistor, Chip, 1/8W, 1%,
54	1	R11	Resistor	Std	Std	300	603	Resistor, Chip, 1/8W, 1%
55	1	R7	Resistor	Std	Std	300k	603	Resistor, Chip, 1/8W, 1%
56	1	R30	Resistor	Std	Std	30k	603	Resistor, Chip, 1/8W, 1%
57	1	R33	Resistor	Std	Std	NC	603	NC
58	1	R10	Resistor	Std	Std	4.7	603	Resistor, Chip, 1/8W, 1%
59	1	R23	Resistor	Std	Std	4.7K	603	Resistor, Chip, 1/8W, 1%
60	1	R25	Resistor	Std	Std	47K	603	Resistor, Chip, 1/8W, 1%
61	1	R32	Resistor	Std	Std	68K	603	Resistor, Chip, 1/8W, 1%
62	1	R24	Resistor	Std	Std	75K	603	Resistor, Chip, 1/8W, 1%
63	1	R20	Resistor	Std	Std	820k	603	Resistor, Chip, 1/8W, 1%
64	1	R37	Resistor	Std	Std	NC	603	NC
65	2	R15-16	Resistor	Std	Std	NC	603	NC
66	2	R4-5	Resistor	ERJ8BQFR062V	Panason	0.62	1206	Resistor, Chip, 1/2W, 1%
67	1	R2	Resistor	Std	Std	10	1206	Resistor, Chip, 1/4W, 1%
68	1	R31	Resistor	Std	Std	1k	805	Resistor, Chip, 1/5W, 1%
69	1	R12	Resistor	Std	Std	20	805	Resistor, Chip, 1/5W, 1%
70	1	R1	Resistor	Std	Std	300k	1206	Resistor, Chip, 1/4W, 1%

DN05104/D
BOM (Continued)

References

ON Semiconductor datasheet for NCP1342/4306/, NTMFS6B03, ATP104

ON Semiconductor Design Notes DN05043

CanYon semiconductor datasheet for WT6632F

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